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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	440
Number of Logic Elements/Cells	3520
Total RAM Bits	81920
Number of I/O	93
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	121-VFBGA
Supplier Device Package	121-UCBGA (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/ice40lp4k-cm121tr

Features

- **Flexible Logic Architecture**
 - Five devices with 384 to 7,680 LUT4s and 10 to 206 I/Os
- **Ultra Low Power Devices**
 - Advanced 40 nm low power process
 - As low as 21 μ A standby power
 - Programmable low swing differential I/Os
- **Embedded and Distributed Memory**
 - Up to 128 kbits sysMEM™ Embedded Block RAM
- **Pre-Engineered Source Synchronous I/O**
 - DDR registers in I/O cells
- **High Current LED Drivers**
 - Three High Current Drivers used for three different LEDs or one RGB LED
- **High Performance, Flexible I/O Buffer**
 - Programmable sysIO™ buffer supports wide range of interfaces:
 - LVCMOS 3.3/2.5/1.8
 - LVDS25E, subLVDS
 - Schmitt trigger inputs, to 200 mV typical hysteresis
 - Programmable pull-up mode
- **Flexible On-Chip Clocking**
 - Eight low-skew global clock resources
 - Up to two analog PLLs per device
- **Flexible Device Configuration**
 - SRAM is configured through:
 - Standard SPI Interface
 - Internal Nonvolatile Configuration Memory (NVCN)
- **Broad Range of Package Options**
 - WLCSP, QFN, VQFP, TQFP, ucBGA, caBGA, and csBGA package options
 - Small footprint package options
 - As small as 1.40 mm x 1.48 mm
 - Advanced halogen-free packaging

Table 1-1. iCE40 Family Selection Guide

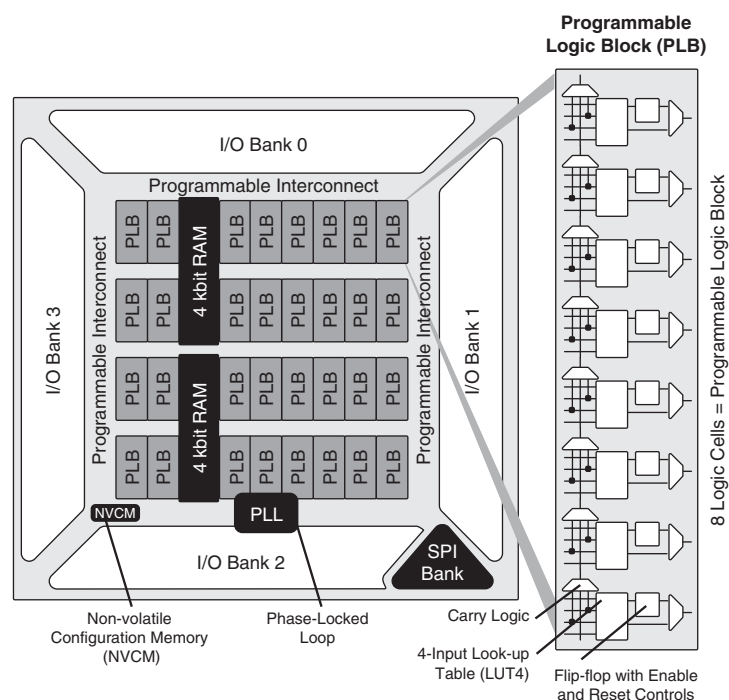
Part Number		LP384	LP640	LP1K	LP4K	LP8K	HX1K	HX4K	HX8K
Logic Cells (LUT + Flip-Flop)		384	640	1,280	3,520	7,680	1,280	3,520	7,680
RAM4K Memory Blocks		0	8	16	20	32	16	20	32
RAM4K RAM bits		0	32K	64K	80K	128K	64K	80K	128K
Phase-Locked Loops (PLLs)		0	0	1 ¹	2 ²	2 ²	1 ¹	2	2
Maximum Programmable I/O Pins		63	25	95	167	178	95	95	206
Maximum Differential Input Pairs		8	3	12	20	23	11	12	26
High Current LED Drivers		0	3	3	0	0	0	0	0
Package	Code	Programmable I/O: Max Inputs (LVDS25)							
16 WLCSP (1.40 mm x 1.48 mm, 0.35 mm)	SWG16		10(0) ¹	10(0) ¹					
32 QFN (5 mm x 5 mm, 0.5 mm)	SG32	21(3)							
36 ucBGA (2.5 mm x 2.5 mm, 0.4 mm)	CM36	25(3)		25(3) ¹					
49 ucBGA (3 mm x 3 mm, 0.4 mm)	CM49	37(6)		35(5) ¹					
81 ucBGA (4 mm x 4 mm, 0.4 mm)	CM81			63(8)	63(9) ²	63(9) ²			
81 csBGA (5 mm x 5 mm, 0.5 mm)	CB81			62(9) ¹					

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Architecture Overview

The iCE40 family architecture contains an array of Programmable Logic Blocks (PLB), sysCLOCK™ PLLs, Non-volatile Programmable Configuration Memory (NVCM) and blocks of sysMEM™ Embedded Block RAM (EBR) surrounded by Programmable I/O (PIO). Figure 2-1 shows the block diagram of the iCE40LP/HX1K device.

Figure 2-1. iCE40LP/HX1K Device, Top View



The logic blocks, Programmable Logic Blocks (PLB) and sysMEM EBR blocks, are arranged in a two-dimensional grid with rows and columns. Each column has either logic blocks or EBR blocks. The PIO cells are located at the periphery of the device, arranged in banks. The PLB contains the building blocks for logic, arithmetic, and register functions. The PIOs utilize a flexible I/O buffer referred to as a sysIO buffer that supports operation with a variety of interface standards. The blocks are connected with many vertical and horizontal routing channel resources. The place and route software tool automatically allocates these routing resources.

In the iCE40 family, there are up to four independent sysIO banks. Note on some packages V_{CCIO} banks are tied together. There are different types of I/O buffers on the different banks. Refer to the details in later sections of this document. The sysMEM EBRs are large 4 kbit, dedicated fast memory blocks. These blocks can be configured as RAM, ROM or FIFO.

The iCE40 architecture also provides up to two sysCLOCK Phase Locked Loop (PLL) blocks. The PLLs have multiply, divide, and phase shifting capabilities that are used to manage the frequency and phase relationships of the clocks.

Every device in the family has a SPI port that supports programming and configuration of the device. The iCE40 includes on-chip, Nonvolatile Configuration Memory (NVCM).

RAM Initialization and ROM Operation

If desired, the contents of the RAM can be pre-loaded during device configuration.

By preloading the RAM block during the chip configuration cycle and disabling the write controls, the sysMEM block can also be utilized as a ROM.

Note the sysMEM Embedded Block RAM Memory address 0 cannot be initialized.

Memory Cascading

Larger and deeper blocks of RAM can be created using multiple EBR sysMEM Blocks.

RAM4k Block

Figure 2-4 shows the 256x16 memory configurations and their input/output names. In all the sysMEM RAM modes, the input data and addresses for the ports are registered at the input of the memory array.

Figure 2-4. sysMEM Memory Primitives

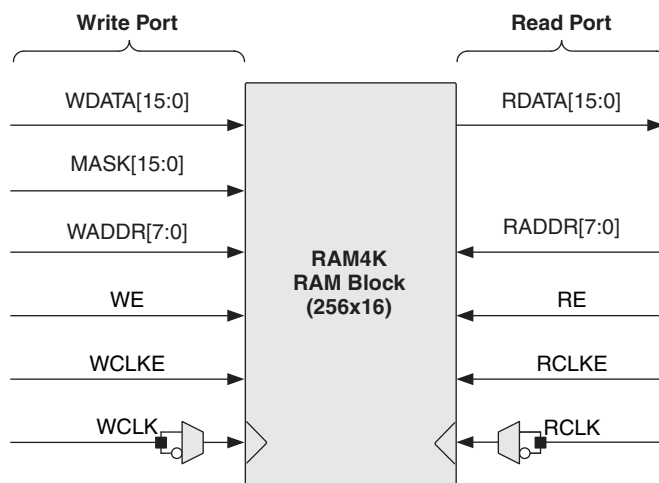


Table 2-5. EBR Signal Descriptions

Signal Name	Direction	Description
WDATA[15:0]	Input	Write Data input.
MASK[15:0]	Input	Masks write operations for individual data bit-lines. 0 = write bit; 1 = don't write bit
WADDR[7:0]	Input	Write Address input. Selects one of 256 possible RAM locations.
WE	Input	Write Enable input.
WCLKE	Input	Write Clock Enable input.
WCLK	Input	Write Clock input. Default rising-edge, but with falling-edge option.
RDATA[15:0]	Output	Read Data output.
RADDR[7:0]	Input	Read Address input. Selects one of 256 possible RAM locations.
RE	Input	Read Enable input.
RCLKE	Input	Read Clock Enable input.
RCLK	Input	Read Clock input. Default rising-edge, but with falling-edge option.

For further information on the sysMEM EBR block, please refer to TN1250, [Memory Usage Guide for iCE40 Devices](#).

sysIO

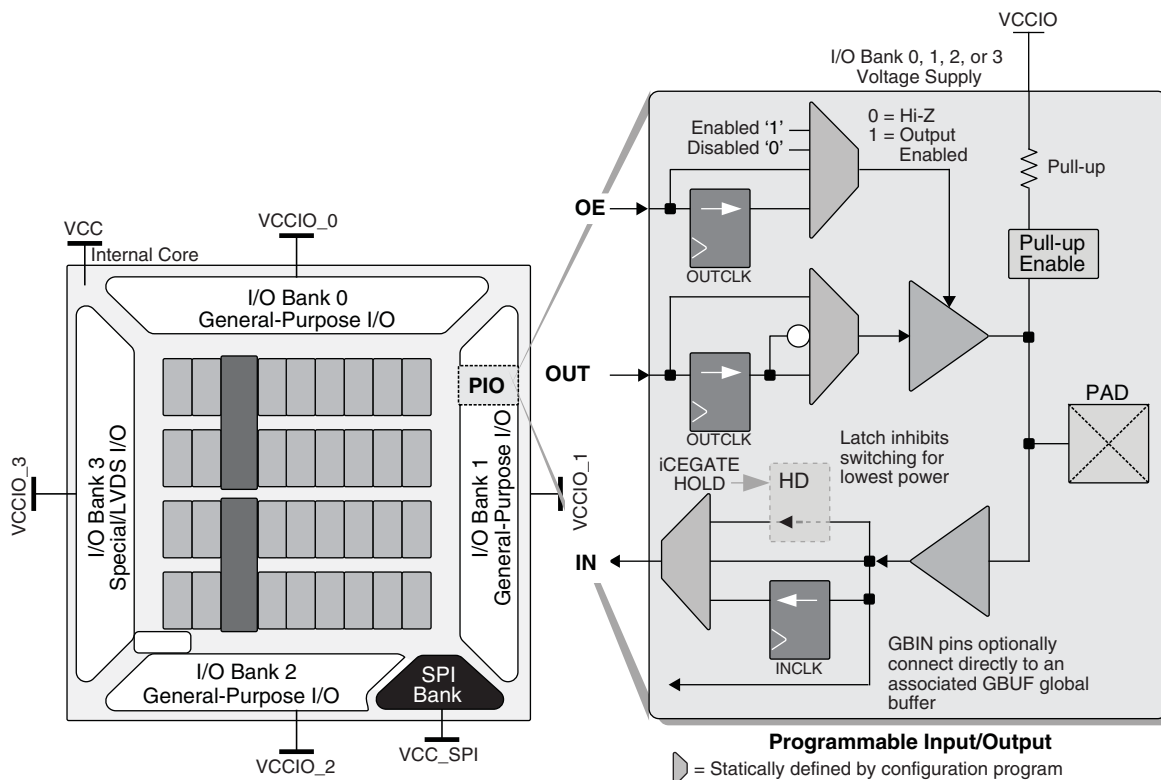
Buffer Banks

iCE40 devices have up to four I/O banks with independent V_{CCIO} rails with an additional configuration bank V_{CC_SPI} for the SPI I/Os.

Programmable I/O (PIO)

The programmable logic associated with an I/O is called a PIO. The individual PIO are connected to their respective sysIO buffers and pads. The PIOs are placed on all four sides of the device.

Figure 2-5. I/O Bank and Programmable I/O Cell



The PIO contains three blocks: an input register block, output register block iCEgate™ and tri-state register block. To save power, the optional iCEgate™ latch can selectively freeze the state of individual, non-registered inputs within an I/O bank. Note that the freeze signal is common to the bank. These blocks can operate in a variety of modes along with the necessary clock and selection logic.

Input Register Block

The input register blocks for the PIOs on all edges contain registers that can be used to condition high-speed interface signals before they are passed to the device core. In Generic DDR mode, two registers are used to sample the data on the positive and negative edges of the system clock signal, creating two data streams.

Output Register Block

The output register block can optionally register signals from the core of the device before they are passed to the sysIO buffers. In Generic DDR mode, two registers are used to capture the data on the positive and negative edge of the system clock and then muxed creating one data stream.

Figure 2-6 shows the input/output register block for the PIOs.

Figure 2-6. iCE I/O Register Block Diagram

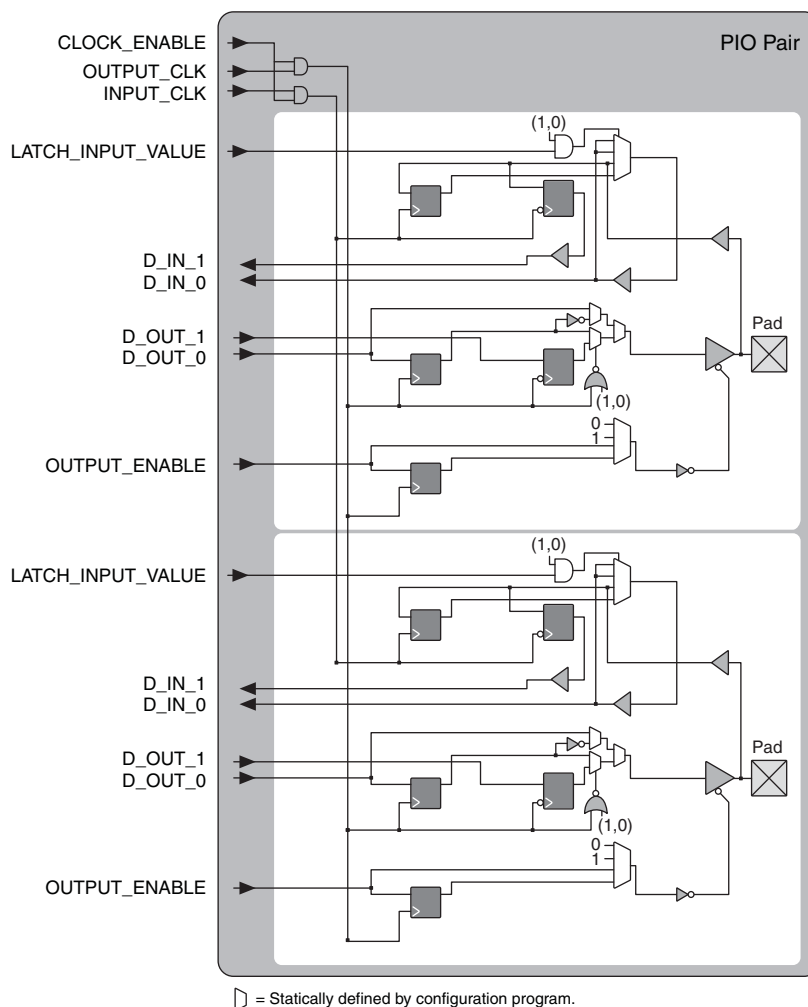


Table 2-6. PIO Signal List

Pin Name	I/O Type	Description
OUTPUT_CLK	Input	Output register clock
CLOCK_ENABLE	Input	Clock enable
INPUT_CLK	Input	Input register clock
OUTPUT_ENABLE	Input	Output enable
D_OUT_0/1	Input	Data from the core
D_IN_0/1	Output	Data to the core
LATCH_INPUT_VALUE	Input	Latches/holds the Input Value

sysIO Buffer

Each I/O is associated with a flexible buffer referred to as a sysIO buffer. These buffers are arranged around the periphery of the device in groups referred to as banks. The sysIO buffers allow users to implement a wide variety of standards that are found in today's systems including LVCMOS and LVDS25.

High Current LED Drivers combine three sysIO buffers together. This allows for programmable drive strength. This also allows for high current drivers that are ideal to drive three white LEDs, or one RGB LED. Each bank is capable of supporting multiple I/O standards including single-ended LVCMOS buffers and differential LVDS25E output buf-

Power On Reset

iCE40 devices have power-on reset circuitry to monitor V_{CC} , V_{CCIO_2} , V_{PP_2V5} , and V_{CC_SPI} voltage levels during power-up and operation. At power-up, the POR circuitry monitors V_{CC} , V_{CCIO_2} , V_{PP_2V5} , and V_{CC_SPI} (controls configuration) voltage levels. It then triggers download from the on-chip NVCM or external Flash memory after reaching the power-up levels specified in the Power-On-Reset Voltage table in the DC and Switching Characteristics section of this data sheet. Before and during configuration, the I/Os are held in tri-state. I/Os are released to user functionality once the device has finished configuration.

Programming and Configuration

This section describes the programming and configuration of the iCE40 family.

Device Programming

The NVCM memory can be programmed through the SPI port.

Device Configuration

There are various ways to configure the Configuration RAM (CRAM) including:

1. Internal NVCM Download
2. From a SPI Flash (Master SPI mode)
3. System microprocessor to drive a Serial Slave SPI port (SSPI mode)

The image to configure the CRAM can be selected by the user on power up (Cold Boot) or once powered up (Warm Boot).

For more details on programming and configuration, see TN1248, [iCE40 Programming and Configuration Usage Guide](#).

Power Saving Options

iCE40 devices are available in two options for maximum flexibility: LP and HX devices. The LP devices have ultra low static and dynamic power consumption. HX devices are designed to provide high performance. Both the LP and the HX devices operate at 1.2 V V_{CC} .

iCE40 devices feature iCEGate and PLL low power mode to allow users to meet the static and dynamic power requirements of their applications. While these features are available in both device types, these features are mainly intended for use with iCE40 LP devices to manage power consumption.

Table 2-9. iCE40 Power Saving Features Description

Device Subsystem	Feature Description
PLL	When LATCHINPUTVALUE is enabled, forces the PLL into low-power mode; PLL output held static at last input clock value.
iCEGate	To save power, the optional iCEgate latch can selectively freeze the state of individual, non-registered inputs within an I/O bank. Registered inputs are effectively frozen by their associated clock or clock-enable control.

Static Supply Current – HX Devices^{1, 2, 3, 4}

Symbol	Parameter	Device	Typ. V_{CC}^4	Units
I_{CC}	Core Power Supply	iCE40HX1K	296	μA
		iCE40HX4K	1140	μA
		iCE40HX8K	1140	μA
I_{CCPLL}^5	PLL Power Supply	All devices	0.5	μA
I_{PP_2V5}	NVCM Power Supply	All devices	1.0	μA
I_{CCIO}, I_{CC_SPI}	Bank Power Supply ⁴ $V_{CCIO} = 2.5 V$	All devices	3.5	μA

1. Assumes blank pattern with the following characteristics: all outputs are tri-stated, all inputs are configured as LVCMOS and held at V_{CCIO} or GND, on-chip PLL is off. For more detail with your specific design, use the Power Calculator tool. Power specified with master SPI configuration mode. Other modes may be up to 25% higher.
2. Frequency = 0 MHz.
3. $T_J = 25^\circ C$, power supplies at nominal voltage.
4. Does not include pull-up.
5. V_{CCPLL} is tied to V_{CC} internally in packages without PLLs pins.

Programming NVCM Supply Current – LP Devices^{1, 2, 3, 4}

Symbol	Parameter	Device	Typ. V_{CC}^5	Units
I_{CC}	Core Power Supply	iCE40LP384	60	μA
		iCE40LP640	120	μA
		iCE40LP1K	120	μA
		iCE40LP4K	350	μA
		iCE40LP8K	350	μA
$I_{CCPLL}^{6, 7}$	PLL Power Supply	All devices	0.5	μA
I_{PP_2V5}	NVCM Power Supply	All devices	2.5	mA
I_{CCIO}^8, I_{CC_SPI}	Bank Power Supply ⁵	All devices	3.5	mA

1. Assumes all inputs are held at V_{CCIO} or GND and all outputs are tri-stated.
2. Typical user pattern.
3. SPI programming is at 8 MHz.
4. $T_J = 25^\circ C$, power supplies at nominal voltage.
5. Per bank. $V_{CCIO} = 2.5 V$. Does not include pull-up.
6. No PLL available on the iCE40-LP384 and iCE40-LP640 device.
7. V_{CCPLL} is tied to V_{CC} internally in packages without PLLs pins.
8. V_{PP_FAST} , used only for fast production programming, must be left floating or unconnected in applications, except CM36 and CM49 packages MUST have the V_{PP_FAST} ball connected to V_{CCIO_0} ball externally.

Peak Startup Supply Current – HX Devices

Symbol	Parameter	Device	Max	Units
I_{CCPEAK}	Core Power Supply	iCE40HX1K	6.9	mA
		iCE40HX4K	22.3	mA
		iCE40HX8K	22.3	mA
$I_{CCPLLPEAK}^1$	PLL Power Supply	iCE40HX1K	1.8	mA
		iCE40HX4K	6.4	mA
		iCE40HX8K	6.4	mA
$I_{PP_2V5PEAK}$	NVCM Power Supply	iCE40HX1K	2.8	mA
		iCE40HX4K	4.1	mA
		iCE40HX8K	4.1	mA
$I_{CCIOPEAK}, I_{CC_SPIPEAK}$	Bank Power Supply	iCE40HX1K	6.8	mA
		iCE40HX4K	6.8	mA
		iCE40HX8K	6.8	mA

1. V_{CCPLL} is tied to V_{CC} internally in packages without PLLs pins.

sysIO Recommended Operating Conditions

Standard	V_{CCIO} (V)		
	Min.	Typ.	Max.
LVC MOS 3.3	3.14	3.3	3.46
LVC MOS 2.5	2.37	2.5	2.62
LVC MOS 1.8	1.71	1.8	1.89
LVDS25E ^{1,2}	2.37	2.5	2.62
subLVDS ^{1,2}	1.71	1.8	1.89

1. Inputs on-chip. Outputs are implemented with the addition of external resistors.

2. Does not apply to Configuration Bank V_{CC_SPI} .

sysIO Single-Ended DC Electrical Characteristics

Input/ Output Standard	V_{IL}		V_{IH}^1		V_{OL} Max. (V)	V_{OH} Min. (V)	I_{OL} Max. (mA)	I_{OH} Max. (mA)
	Min. (V)	Max. (V)	Min. (V)	Max. (V)				
LVC MOS 3.3	-0.3	0.8	2.0	$V_{CCIO} + 0.2$ V	0.4	$V_{CCIO} - 0.4$	8, 16 ² , 24 ²	-8, -16 ² , -24 ²
					0.2	$V_{CCIO} - 0.2$	0.1	-0.1
LVC MOS 2.5	-0.3	0.7	1.7	$V_{CCIO} + 0.2$ V	0.4	$V_{CCIO} - 0.4$	6, 12 ² , 18 ²	-6, -12 ² , -18 ²
					0.2	$V_{CCIO} - 0.2$	0.1	-0.1
LVC MOS 1.8	-0.3	0.35 V_{CCIO}	0.65 V_{CCIO}	$V_{CCIO} + 0.2$ V	0.4	$V_{CCIO} - 0.4$	4, 8 ² , 12 ²	-4, -8 ² , -12 ²
					0.2	$V_{CCIO} - 0.2$	0.1	-0.1

1. Some products are clamped to a diode when V_{IN} is larger than V_{CCIO} .

2. Only for High Drive LED outputs.

LVDS25E Emulation

iCE40 devices can support LVDS25E outputs via emulation on all banks. The output is emulated using complementary LVCMOS outputs in conjunction with resistors across the driver outputs on all devices. The scheme shown in Figure 3-1 is one possible solution for LVDS25E standard implementation. Resistor values in Figure 3-1 are industry standard values for 1% resistors.

Figure 3-1. LVDS25E Using External Resistors

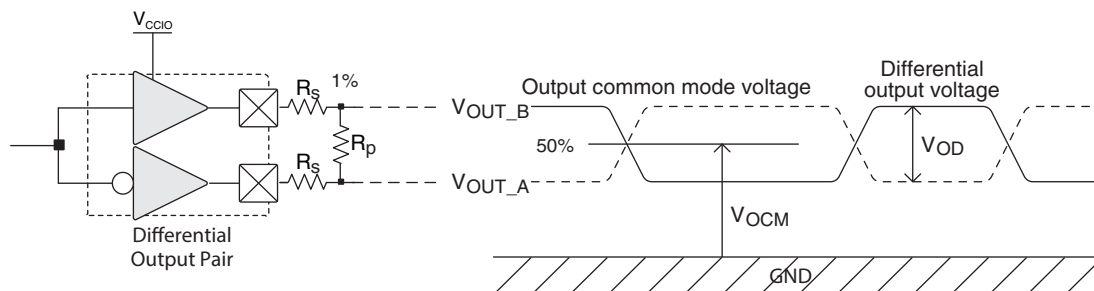


Table 3-1. LVDS25E DC Conditions

Over Recommended Operating Conditions

Parameter	Description	Typ.	Units
Z_{OUT}	Output impedance	20	Ohms
R_S	Driver series resistor	150	Ohms
R_P	Driver parallel resistor	140	Ohms
R_T	Receiver termination	100	Ohms
V_{OH}	Output high voltage	1.43	V
V_{OL}	Output low voltage	1.07	V
V_{OD}	Output differential voltage	0.30	V
V_{CM}	Output common mode voltage	1.25	V
Z_{BACK}	Back impedance	100.5	Ohms
I_{DC}	DC output current	6.03	mA

Typical Building Block Function Performance – LP Devices^{1, 2}

Pin-to-Pin Performance (LVCMOS25)

Function	Timing	Units
Basic Functions		
16-bit decoder	11.0	ns
4:1 MUX	12.0	ns
16:1 MUX	13.0	ns

Register-to-Register Performance

Function	Timing	Units
Basic Functions		
16:1 MUX	190	MHz
16-bit adder	160	MHz
16-bit counter	175	MHz
64-bit counter	65	MHz
Embedded Memory Functions		
256x16 Pseudo-Dual Port RAM	240	MHz

1. The above timing numbers are generated using the iCECube2 design tool. Exact performance may vary with device and tool version. The tool uses internal parameters that have been characterized but are not tested on every device.
2. Using a V_{CC} of 1.14 V at Junction Temp 85 °C.

Typical Building Block Function Performance – HX Devices^{1, 2}

Pin-to-Pin Performance (LVCMOS25)

Function	Timing	Units
Basic Functions		
16-bit decoder	10.0	ns
4:1 MUX	9.0	ns
16:1 MUX	9.5	ns

Register-to-Register Performance

Function	Timing	Units
Basic Functions		
16:1 MUX	305	MHz
16-bit adder	220	MHz
16-bit counter	255	MHz
64-bit counter	105	MHz
Embedded Memory Functions		
256x16 Pseudo-Dual Port RAM	403	MHz

1. The above timing numbers are generated using the iCECube2 design tool. Exact performance may vary with device and tool version. The tool uses internal parameters that have been characterized but are not tested on every device.
2. Using a V_{CC} of 1.14 V at Junction Temp 85 °C.

Derating Logic Timing

Logic timing provided in the following sections of the data sheet and the Lattice design tools are worst case numbers in the operating range. Actual delays may be much faster. Lattice design tools can provide logic timing numbers at a particular temperature and voltage.

Maximum sysIO Buffer Performance²

I/O Standard	Max. Speed	Units
Inputs		
LVDS25 ¹	400	MHz
subLVDS18 ¹	400	MHz
LVC MOS33	250	MHz
LVC MOS25	250	MHz
LVC MOS18	250	MHz
Outputs		
LVDS25E	250	MHz
subLVDS18E	155	MHz
LVC MOS33	250	MHz
LVC MOS25	250	MHz
LVC MOS18	155	MHz

1. Supported in Bank 3 only.

2. Measured with a toggling pattern

iCE40 Family Timing Adders

Over Recommended Commercial Operating Conditions - LP Devices^{1, 2, 3, 4, 5}

Buffer Type	Description	Timing	Units
Input Adjusters			
LVDS25	LVDS, $V_{CCIO} = 2.5\text{ V}$	-0.18	ns
subLVDS	subLVDS, $V_{CCIO} = 1.8\text{ V}$	0.82	ns
LVC MOS33	LVC MOS, $V_{CCIO} = 3.3\text{ V}$	0.18	ns
LVC MOS25	LVC MOS, $V_{CCIO} = 2.5\text{ V}$	0.00	ns
LVC MOS18	LVC MOS, $V_{CCIO} = 1.8\text{ V}$	0.19	ns
Output Adjusters			
LVDS25E	LVDS, Emulated, $V_{CCIO} = 2.5\text{ V}$	0.00	ns
subLVDS E	subLVDS, Emulated, $V_{CCIO} = 1.8\text{ V}$	1.32	ns
LVC MOS33	LVC MOS, $V_{CCIO} = 3.3\text{ V}$	-0.12	ns
LVC MOS25	LVC MOS, $V_{CCIO} = 2.5\text{ V}$	0.00	ns
LVC MOS18	LVC MOS, $V_{CCIO} = 1.8\text{ V}$	1.32	ns

1. Timing adders are relative to LVC MOS25 and characterized but not tested on every device.

2. LVC MOS timing measured with the load specified in Switching Test Condition table.

3. All other standards tested according to the appropriate specifications.

4. Commercial timing numbers are shown.

5. Not all I/O standards are supported for all banks. See the Architecture section of this data sheet for details.

iCE40 External Switching Characteristics – LP Devices ^{1, 2}
Over Recommended Operating Conditions

Parameter	Description	Device	Min.	Max.	Units
Clocks					
Global Clocks					
f _{MAX_GBUF}	Frequency for Global Buffer Clock network	All iCE40LP devices	—	275	MHz
t _{W_GBUF}	Clock Pulse Width for Global Buffer	All iCE40LP devices	0.92	—	ns
t _{SKEW_GBUF}	Global Buffer Clock Skew Within a Device	iCE40LP384	—	370	ps
		iCE40LP640	—	230	ps
		iCE40LP1K	—	230	ps
		iCE40LP4K	—	340	ps
		iCE40LP8K	—	340	ps
Pin-LUT-Pin Propagation Delay					
t _{PD}	Best case propagation delay through one LUT-4	All iCE40LP devices	—	9.36	ns
General I/O Pin Parameters (Using Global Buffer Clock without PLL) ³					
t _{SKEW_IO}	Data bus skew across a bank of IOs	iCE40LP384	—	300	ps
		iCE40LP640	—	200	ps
		iCE40LP1K	—	200	ps
		iCE40LP4K	—	280	ps
		iCE40LP8K	—	280	ps
t _{CO}	Clock to Output - PIO Output Register	iCE40LP384	—	6.33	ns
		iCE40LP640	—	5.91	ns
		iCE40LP1K	—	5.91	ns
		iCE40LP4K	—	6.58	ns
		iCE40LP8K	—	6.58	ns
t _{SU}	Clock to Data Setup - PIO Input Register	iCE40LP384	−0.08	—	ns
		iCE40LP640	−0.33	—	ns
		iCE40LP1K	−0.33	—	ns
		iCE40LP4K	−0.63	—	ns
		iCE40LP8K	−0.63	—	ns
t _H	Clock to Data Hold - PIO Input Register	iCE40LP384	1.99	—	ns
		iCE40LP640	2.81	—	ns
		iCE40LP1K	2.81	—	ns
		iCE40LP4K	3.48	—	ns
		iCE40LP8K	3.48	—	ns
General I/O Pin Parameters (Using Global Buffer Clock with PLL) ³					
t _{COPLL}	Clock to Output - PIO Output Register	iCE40LP1K	—	2.20	ns
		iCE40LP4K	—	2.30	ns
		iCE40LP8K	—	2.30	ns
t _{SUPLL}	Clock to Data Setup - PIO Input Register	iCE40LP1K	5.23	—	ns
		iCE40LP4K	6.13	—	ns
		iCE40LP8K	6.13	—	ns

iCE40 External Switching Characteristics – LP Devices (Continued)^{1, 2}
Over Recommended Operating Conditions

Parameter	Description	Device	Min.	Max.	Units
t _{HPLL}	Clock to Data Hold - PIO Input Register	iCE40LP1K	–0.90	—	ns
		iCE40LP4K	–0.80	—	ns
		iCE40LP8K	–0.80	—	ns

1. Exact performance may vary with device and design implementation. Commercial timing numbers are shown at 85 °C and 1.14 V. Other operating conditions can be extracted from the iCECube2 software.

2. General I/O timing numbers based on LVCMOS 2.5, 0pf load.

3. Supported on devices with a PLL.

iCE40 External Switching Characteristics – HX Devices ^{1, 2}

Over Recommended Operating Conditions

Parameter	Description	Device	Min.	Max.	Units
Clocks					
Primary Clocks					
f _{MAX_GBUF}	Frequency for Global Buffer Clock network	All iCE40HX devices	—	275	MHz
t _{W_GBUF}	Clock Pulse Width for Global Buffer	All iCE40HX devices	0.88	—	ns
t _{SKEW_GBUF}	Global Buffer Clock Skew Within a Device	iCE40HX1K	—	727	ps
		iCE40HX4K	—	300	ps
		iCE40HX8K	—	300	ps
Pin-LUT-Pin Propagation Delay					
t _{PD}	Best case propagation delay through one LUT-4	All iCE40 HX devices	—	7.30	ns
General I/O Pin Parameters (Using Global Buffer Clock without PLL)					
t _{SKEW_IO}	Data bus skew across a bank of IOs	iCE40HX1K	—	696	ps
		iCE40HX4K	—	290	ps
		iCE40HX8K	—	290	ps
t _{CO}	Clock to Output - PIO Output Register	iCE40HX1K	—	5.00	ns
		iCE40HX4K	—	5.41	ns
		iCE40HX8K	—	5.41	ns
t _{SU}	Clock to Data Setup - PIO Input Register	iCE40HX1K	−0.23	—	ns
		iCE40HX4K	−0.43	—	ns
		iCE40HX8K	−0.43	—	ns
t _H	Clock to Data Hold - PIO Input Register	iCE40HX1K	1.92	—	ns
		iCE40HX4K	2.38	—	ns
		iCE40HX8K	2.38	—	ns
General I/O Pin Parameters (Using Global Buffer Clock with PLL) ³					
t _{COPLL}	Clock to Output - PIO Output Register	iCE40HX1K	—	2.96	ns
		iCE40HX4K	—	2.51	ns
		iCE40HX8K	—	2.51	ns
t _{SUPLL}	Clock to Data Setup - PIO Input Register	iCE40HX1K	3.10	—	ns
		iCE40HX4K	4.16	—	ns
		iCE40HX8K	4.16	—	ns
t _{HPLL}	Clock to Data Hold - PIO Input Register	iCE40HX1K	−0.60	—	ns
		iCE40HX4K	−0.53	—	ns
		iCE40HX8K	−0.53	—	ns

1. Exact performance may vary with device and design implementation. Commercial timing numbers are shown at 85 °C and 1.14 V. Other operating conditions, including industrial, can be extracted from the iCECube2 software.

2. General I/O timing numbers based on LVCMOS 2.5, 0pf load.

3. Supported on devices with a PLL.

sysCONFIG Port Timing Specifications¹

Symbol	Parameter		Min.	Typ.	Max.	Units
All Configuration Modes						
$t_{\text{CRESET_B}}$	Minimum CRESET_B Low pulse width required to restart configuration, from falling edge to rising edge		200	—	—	ns
$t_{\text{DONE_IO}}$	Number of configuration clock cycles after CDONE goes High before the PIO pins are activated		49	—	—	Clock Cycles
Slave SPI						
$t_{\text{CR_SCK}}$	Minimum time from a rising edge on CRESET_B until the first SPI write operation, first SPI_SCK. During this time, the iCE40 device is clearing its internal configuration memory	iCE40LP384	600	-	—	us
		iCE40LP640, iCE40LP/HX1K	800	-	—	us
		iCE40LP/HX4K	1200	-	—	us
		iCE40LP/HX8K	1200	-	—	us
f_{MAX}^1	CCLK clock frequency	Write	1	-	25	MHz
		Read iCE40LP384 ²	-	15	-	MHz
		Read iCE40LP640, iCE40LP/HX1K ²	-	15	-	MHz
		Read iCE40LP/HX4K ²	-	15	-	MHz
		Read iCE40LP/HX8K ²	-	15	-	MHz
t_{CCLKH}	CCLK clock pulse width high		20	—	—	ns
t_{CCLKL}	CCLK clock pulse width low		20	—	—	ns
t_{STSU}	CCLK setup time		12	—	—	ns
t_{STH}	CCLK hold time		12	—	—	ns
t_{STCO}	CCLK falling edge to valid output		13	—	—	ns
Master SPI						
f_{MCLK}	MCLK clock frequency	Off	—	0	—	MHz
		Low Frequency (Default)	—	7.5	—	MHz
		Medium Frequency ³	—	24	—	MHz
		High Frequency ³	—	40	—	MHz

Signal Descriptions

Signal Name	I/O	Descriptions
General Purpose		
IO[Bank]_[Row/Column Number][A/B]	I/O	[Bank] indicates the bank of the device on which the pad is located. [Number] indicates IO number on the device.
IO[Bank]_[Row/Column Number][A/B]	I/O	[Bank] indicates the bank of the device on which the pad is located. [Number] indicates IO number on the device. [A/B] indicates the differential I/O. 'A' = negative input. 'B' = positive input.
HCIO[Bank]_[Number]	I/O	High Current IO. [Bank] indicates the bank of the device on which the pad is located. [Number] indicates IO number.
NC	—	No connect
GND	—	GND – Ground. Dedicated pins. It is recommended that all GNDs are tied together.
VCC	—	VCC – The power supply pins for core logic. Dedicated pins. It is recommended that all VCCs are tied to the same supply.
VCCIO_x	—	VCCIO – The power supply pins for I/O Bank x. Dedicated pins. All VCCIOs located in the same bank are tied to the same supply.
PLL and Global Functions (Used as user-programmable I/O pins when not used for PLL or clock pins)		
VCCPLLx	—	PLL VCC – Power. Dedicated pins. The PLL requires a separate power and ground that is quiet and stable to reduce the output clock jitter of the PLL.
GNDPLLx	—	PLL GND – Ground. Dedicated pins. The sysCLOCK PLL has the DC ground connection made on the FPGA, so the external PLL ground connection (GNDPLL) must NOT be connected to the board's ground.
GBINx	—	Global pads. Two per side.
Programming and Configuration		
CBSEL[0:1]	I/O	Dual function pins. I/Os when not used as CBSEL. Optional ColdBoot configuration SElect input, if ColdBoot mode is enabled.
CRESET_B	I	Configuration Reset, active Low. Dedicated input. No internal pull-up resistor. Either actively drive externally or connect a 10 KOhm pull-up resistor to VCCIO_2.
CDONE	I/O	Configuration Done. Includes a permanent weak pull-up resistor to VCCIO_2. If driving external devices with CDONE output, an external pull-up resistor to VCCIO_2 may be required. Refer to the TN1248, iCE40 Programming and Configuration for more details. Following device configuration the iCE40LP640 and iCE40LP1K in the SWG16 package CDONE pin can be used as a user output.
VCC_SPI	—	SPI interface voltage supply input. Must have a valid voltage even if configuring from NVCM.
SPI_SCK	I/O	Input Configuration Clock for configuring an FPGA in Slave SPI mode. Output Configuration Clock for configuring an FPGA configuration modes.
SPI_SS_B	I/O	SPI Slave Select. Active Low. Includes an internal weak pull-up resistor to VCC_SPI during configuration. During configuration, the logic level sampled on this pin determines the configuration mode used by the iCE40 device. An input when sampled at the start of configuration. An input when in SPI Peripheral configuration mode (SPI_SS_B = Low). An output when in Master SPI Flash configuration mode.
SPI_SI	I/O	Slave SPI serial data input and master SPI serial data output
SPI_SO	I/O	Slave SPI serial data output and master SPI serial data input

Signal Descriptions (Continued)

Signal Name	I/O	Descriptions
VPP_FAST	—	Optional fast NVCM programming supply. V _{PP_FAST} , used only for fast production programming, must be left floating or unconnected in applications, except CM36 and CM49 packages MUST have the V _{PP_FAST} ball connected to V _{CCIO_0} ball externally.
VPP_2V5	—	VPP_2V5 NVCM programming and operating supply

Pin Information Summary (Continued)

	iCE40LP4K			iCE40LP8K			iCE40HX1K		
	CM81	CM121	CM225	CM81	CM121	CM225	VQ100	CB132	TQ144
General Purpose I/O per Bank									
Bank 0	17	23	46	17	23	46	19	24	23
Bank 1	15	21	42	15	21	42	19	25	25
Bank 2	9	19	40	9	19	40	12	20	20
Bank 3	18	26	46	18	26	46	18	22	24
Configuration	4	4	4	4	4	4	4	4	4
Total General Purpose Single Ended I/O	63	93	178	63	93	178	72	95	96
High Current Outputs per Bank									
Bank 0	0	0	0	0	0	0	0	0	0
Bank 1	0	0	0	0	0	0	0	0	0
Bank 2	0	0	0	0	0	0	0	0	0
Bank 3	0	0	0	0	0	0	0	0	0
Total Differential Inputs	0	0	0	0	0	0	0	0	0
Differential Inputs per Bank									
Bank 0	0	0	0	0	0	0	0	0	0
Bank 1	0	0	0	0	0	0	0	0	0
Bank 2	0	0	0	0	0	0	0	0	0
Bank 3	9	13	23	9	13	23	9	11	12
Total Differential Inputs	9	13	23	9	13	23	9	11	12
Dedicated Inputs per Bank									
Bank 0	0	0	0	0	0	0	0	0	0
Bank 1	0	0	1	0	0	1	0	1	1
Bank 2	2	2	2	2	2	2	2	2	2
Bank 3	0	0	0	0	0	0	0	0	0
Configuration	0	0	0	0	0	0	0	0	0
Total Dedicated Inputs	2	2	3	2	2	3	2	3	3
Vccio Pins									
Bank 0	1	1	3	1	1	3	2	2	2
Bank 1	1	1	3	1	1	3	2	2	2
Bank 2	1	1	3	1	1	3	2	2	2
Bank 3	1	2	4	1	2	4	3	3	2
VCC	3	4	8	3	4	8	4	5	4
VCC_SPI	1	1	1	1	1	1	1	1	1
VPP_2V5	1	1	1	1	1	1	1	1	1
VPP_FAST ¹	1	1	1	1	1	1	1	1	1
VCCPLL	1	2	2	1	2	2	0	1	1
GND	5	12	18	5	12	18	10	14	10
NC	0	0	0	0	0	0	0	2	19
Total Count of Bonded Pins	81	121	225	81	121	225	100	132	144

1. VPP_FAST¹ used only for fast production programming, must be left floating or unconnected in applications.



iCE40 LP/HX Family Data Sheet

Revision History

March 2017

Data Sheet DS1040

Date	Version	Section	Change Summary
March 2017	3.3	Introduction	Updated Features section. Added 121-ball caBGA package for ICE40 HX4K/8K to Table 1-1, iCE40 Family Selection Guide.
		Architecture	Updated PLB Blocks section. Changed “subtractors” to “subtractions” in the Carry Logic description.
			Updated Clock/Control Distribution Network section. Switched the “Clock Enable” and the “Reset” headings in Table 2-2, Global Buffer (GBUF) Connections to Programmable Logic Blocks.
		Pinout Information	Updated Pin Information Summary section. Added BG121 information under iCE40HX4K and iCE40HX8K.
		Ordering Information	Updated iCE40 Part Number Description section. Added Shipping Method and BG121 package under High Performance (HX) Devices.
			Updated Ordering Information section. Added part numbers for BG121 under High-Performance Industrial Grade Devices, Halogen Free (RoHS) Packaging.
		Supplemental Information	Corrected reference to “Package Diagrams Data Sheet”.
October 2015	3.2	Introduction	Updated Features section. Added footnote to 16 WLCSP Programmable I/O: Max Inputs (LVDS25) in Table 1-1, iCE40 Family Selection Guide.
		DC and Switching Characteristics	Updated sysCLOCK PLL Timing section. Changed t_{DT} conditions.
			Updated Programming NVCM Supply Current – LP Devices section. Changed I_{PP_2V5} and I_{CCIO} , I_{CC_SPI} units.
March 2015	3.1	DC and Switching Characteristics	Updated sysIO Single-Ended DC Electrical Characteristics section. Changed LVCMOS 3.3 and LVCMOS 2.5 V_{OH} Min. (V) from 0.5 to 0.4.
July 2014	3.0	DC and Switching Characteristics	Revised and/or added Typ. V_{CC} data in the following sections. — Static Supply Current – LP Devices — Static Supply Current – HX Devices — Programming NVCM Supply Current – LP Devices — Programming NVCM Supply Current – HX Devices In each section table, the footnote indicating Advanced device status was removed.
		Pinout Information	Updated Pin Information Summary section. Added footnote 1 to CM49 under iCE40LP1K.
April 2014	02.9	Ordering Information	Changed “i” to “I” in part number description and ordering part numbers.
			Added part numbers to the Ultra Low Power Industrial Grade Devices, Halogen Free (RoHS) Packaging table.

